NSN 5962-01-172-8647

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Body Length:	
0.840 inches	
Body Width:	
Between 0.220 inches and	10.310 inches
Body Height:	
0.140 inches	
Maximum Power Dissipa	ition Rating:
739.0 milliwatts	
Operating Tempurature I	Range:
-55.0/+125.0 degrees cels	ius
Storage Tempurature Ra	inge:
-65.0/+150.0 degrees cels	ius
Features Provided:	
Schottky and monolithic ar	nd programmable and bipolar and 3-state output and high impedance
Inclosure Material:	
Ceramic and glass	
Inclosure Configuration:	
Dual-in-line	
Output Logic Form:	
Transistor-transistor logic	
Input Circuit Pattern:	
10 input	
Case Outline Source And	d Designator:
D-2 mil-m-38510	
Terminal Surface Treatm	ient:
Solder	
Voltage Rating And Type	Per Characteristic:
-0.5 volts power source a	nd 7.0 volts power source
Time Rating Per Chacter	istic:
75.00 nanoseconds propa	agation delay time, low to high level output and 75.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type:	
Rom	
Test Data Document:	
96906-mil-std-883 standar	rd (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quar	ntity:
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

No

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